

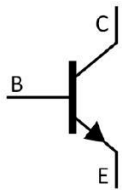
WR0553 M M E QSQ æ M y s ll 1 Silicon NPN transistor in a TO-220 Plastic Package.

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High DC current gain, low saturation voltage, high power dissipation, complementary to 2SB834.

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Audio frequency power amplifier applications.

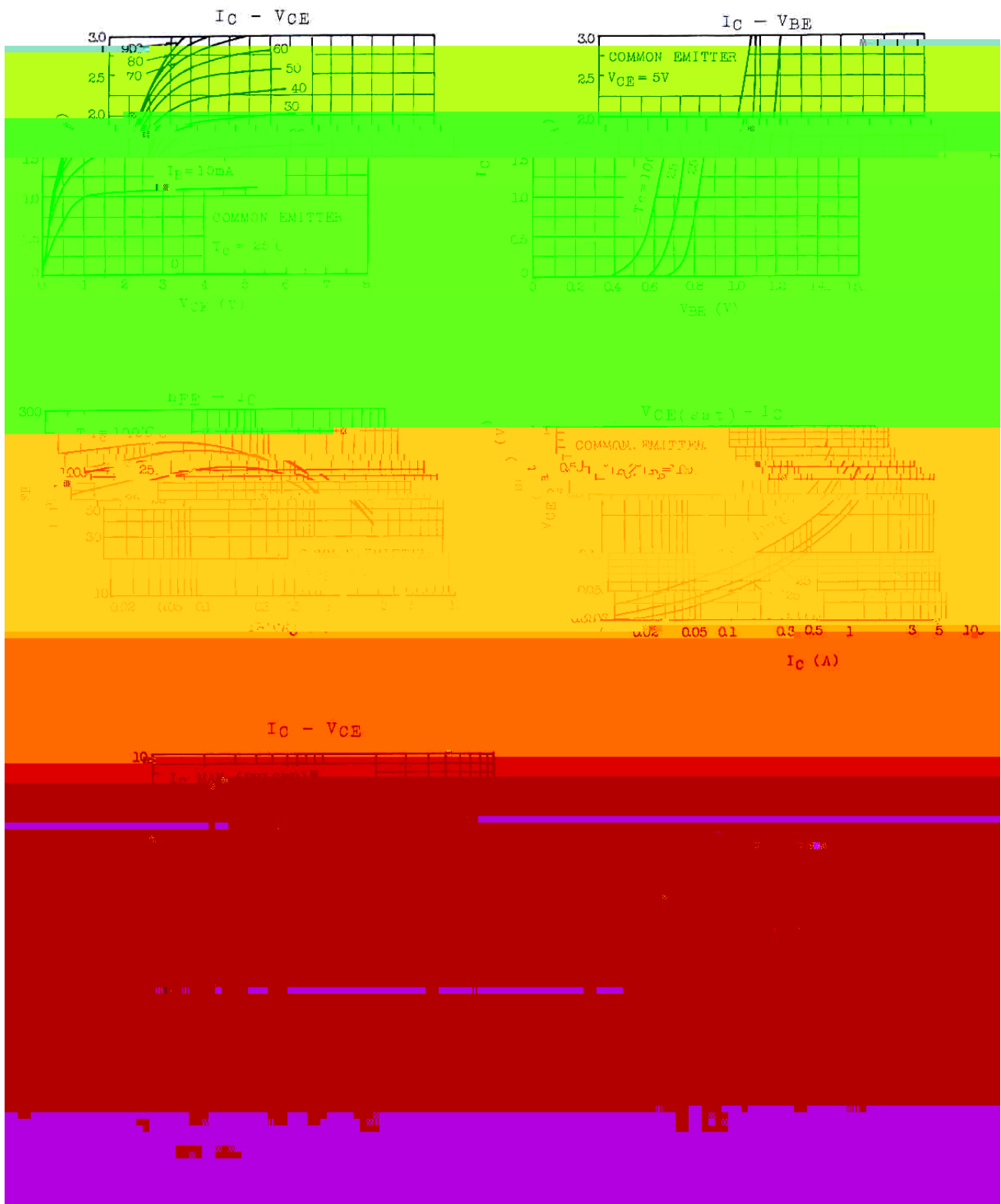


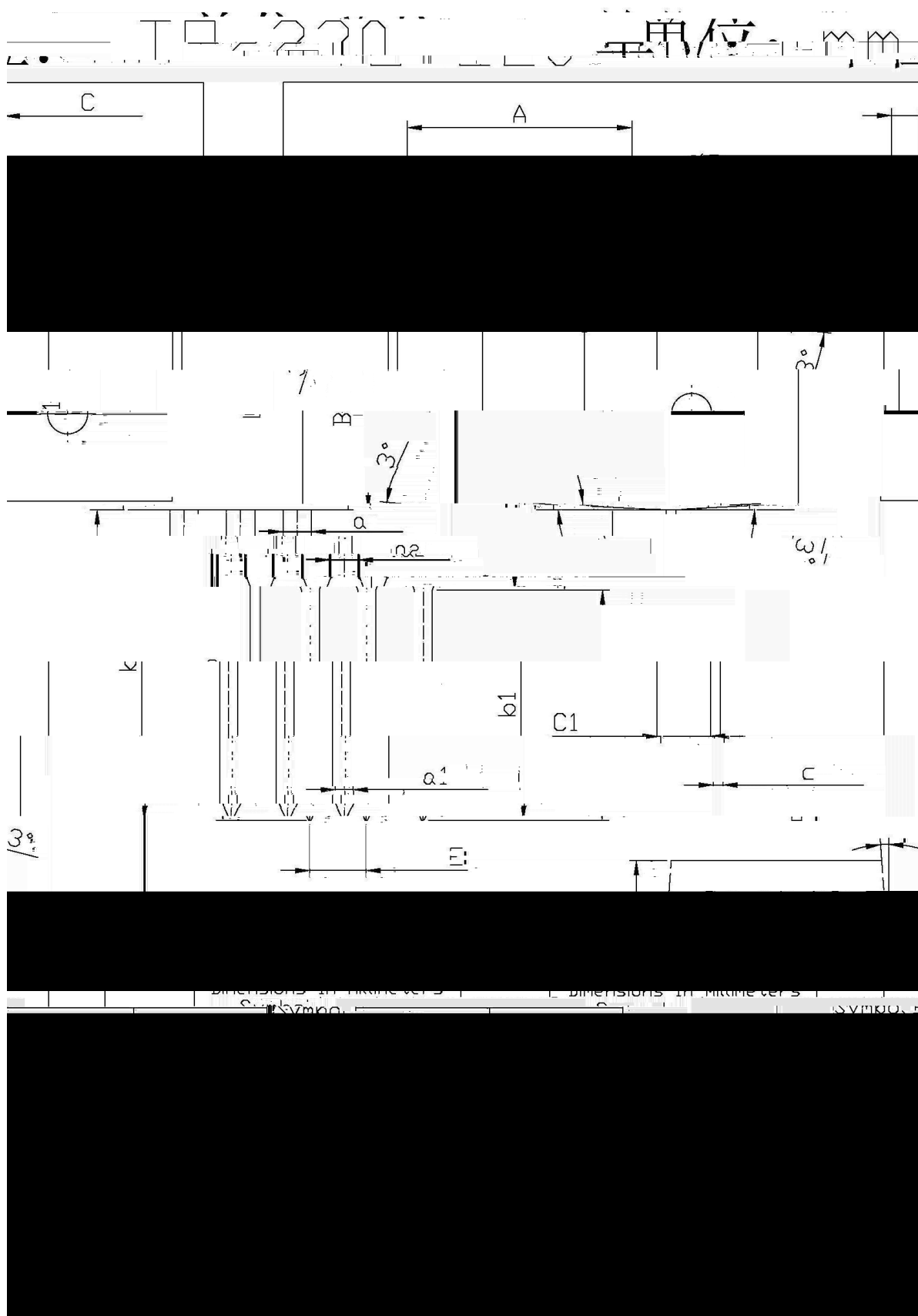
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

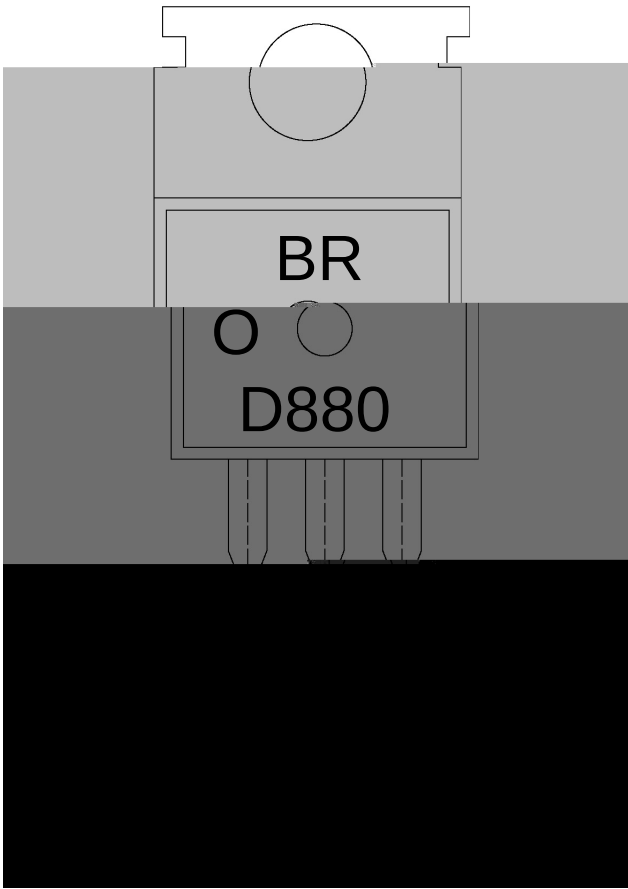
h _{FE} Classifications Symbol	O	Y	GR
h _{FE} Range	60 120	100 200	150 300

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current - Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	1.5	W
	$P_C(T_C=25^\circ\text{C})$	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=50\text{mA}$ $I_B=0$	60			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60\text{V}$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=7.0\text{V}$ $I_C=0$			100	μA







公司代码	公司代码
BR	公司代码
D880	产品型号
R=	h _{FE} 等级
----	产品型号 及 生产年份
Note:	
BR:	Company Code
D880:	Product Type.
O:	h _{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

